

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ a diameter of the fine particle is being 0.1 μm or less.
3. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ a diameter of the fine particle is being 0.01 μm or less.
4. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, claim 35, wherein~~ the fine particle is being electrically charged.
5. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ the fine particle of the raw material species is being gasified before being mixed with the active species.
6. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ the active species is being a radical or an ion.
7. (Currently Amended) The method for manufacturing ceramics according to claim 6, ~~wherein~~ the active species is being a radical or an ion of the raw material species which becomes part of the raw materials for ceramics.
8. (Currently Amended) The method for manufacturing ceramics according to claim 6, ~~wherein~~ the active species is being a radical or an ion of oxygen or nitrogen.
9. (Currently Amended) The method for manufacturing ceramics according to claim 6, ~~wherein~~ the active species is being an ion obtained by activating inert gas.
10. (Currently Amended) The method for manufacturing ceramics according to claim 9, ~~wherein~~ the inert gas is being an ion of argon or xenon.

11. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ at least the active species is being fed to the substrate in an accelerated state.

12-14. (Canceled)

15. (Currently Amended) The method for manufacturing ceramics according to ~~claim 1, wherein claim 35,~~ the ceramic film is being a dielectric.

16. (Currently Amended) The method for manufacturing ceramics according to claim 15, ~~wherein the dielectric is~~ being formed at a temperature of 600°C or less.

17. (Currently Amended) The method for manufacturing ceramics according to claim 15, ~~wherein the dielectric is~~ being formed at a temperature of 450°C or less.

18-34. (Canceled)

35. (Previously Presented) A method for manufacturing ceramics on a substrate, comprising:

mixing a fine particle of a raw material species which becomes at least part of raw materials for ceramics with an active species having high kinetic energy in a mixing chamber;

after mixing the fine particle and active species in the mixing chamber, feeding the mixed fine particle and active species from the mixing chamber to the substrate so that the fine particles of the raw material species are deposited on the substrate while being provided with kinetic energy from the active species; and

increasing the migration energy of atoms in the ceramic film for crystallization of the ceramic film by providing energy to the fine particles of the raw material species by the active species, wherein the ceramic film is formed by an LSMCD process or a misted CVD process.

36. (New) The method for manufacturing ceramics according to claim 35, further comprising:

forming a film-forming region having affinity to ceramics to be formed, and a non-film-forming region having no affinity to the ceramics to be formed, thereby self-alignably forming a ceramic film on a film-forming region, the film-forming region being the partial portion of the substrate.

37. (New) The method for manufacturing ceramics according to claim 35, further comprising:

biasing the substrate holder to accelerate the complex of the active species and the fine particle of the raw material species during deposition.